

SJPB-H9

Schottky Barrier Rectifier

Mar. 2008

General Description

SJPB-H9 is a Schottky Barrier Diode, and has achieved low leakage current and low VF by selecting the best barrier metal.

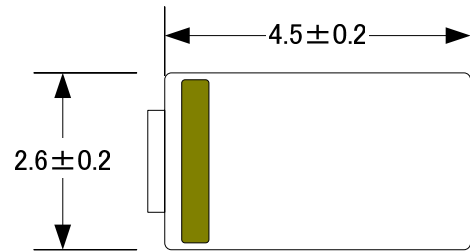
Applications

- DC-DC converters
- AC adapter
- High frequency rectification circuit

Features

- Super-high speed & low noise switching.
- Low forward voltage drop.

Package

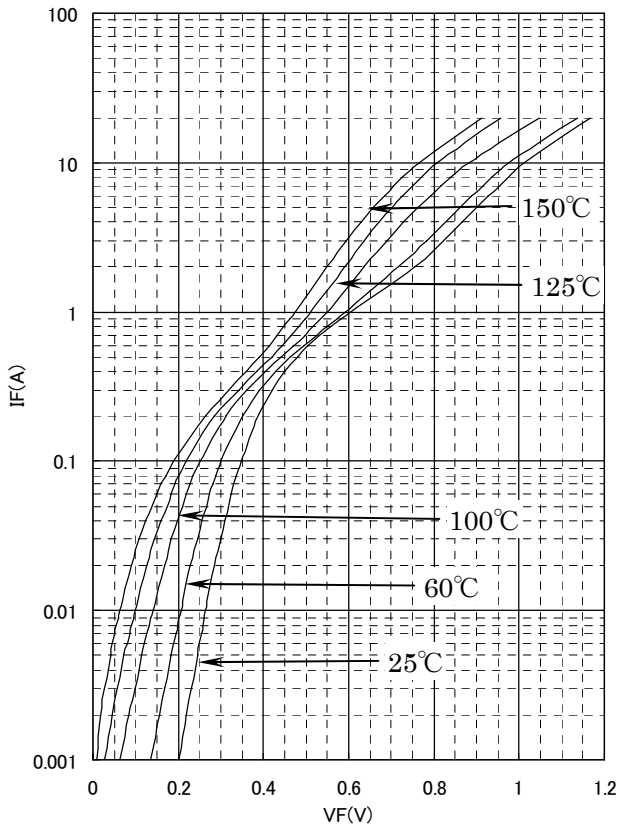


Key Specifications

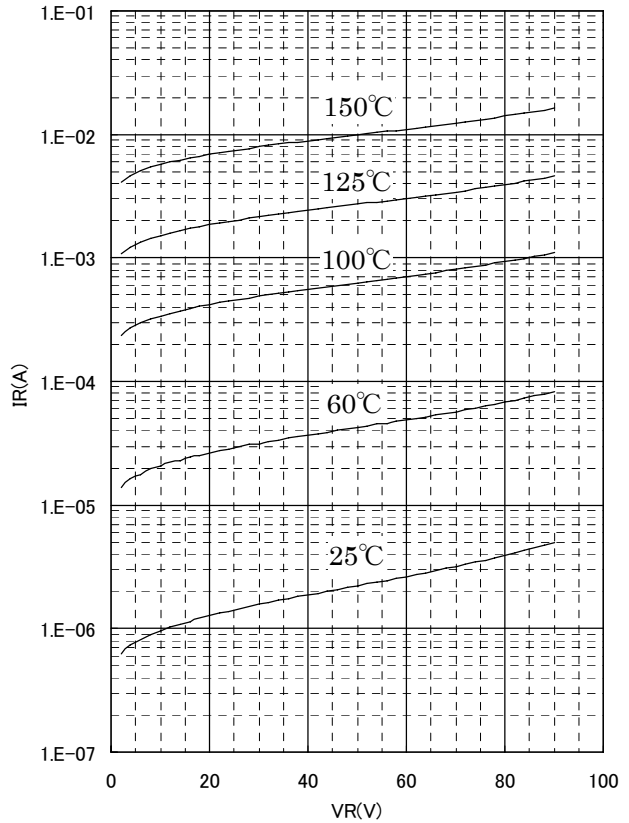
| Symbol | Unit | Rating | Conditions |
|-------------|------|--------|------------|
| V_{RM} | V | 90 | |
| V_F | V | 0.85 | $I_F=2.0A$ |
| $I_{F(AV)}$ | A | 2.0 | |

Typical Characteristics

SJPB-H9 I_F - V_F Characteristics



SJPB-H9 V_R - I_R Characteristics



The information included herein is believed to be accurate and reliable. However, SANKEN ELECTRIC CO., LTD assumes no responsibility for its use ; nor for any infringements of patents or other rights of third parties that may result from its use.

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* Absolute maximum ratings

| No. | Parameter | Symbol | Unit | Rating | Conditions |
|-----|--------------------------------|-------------|-------------|-------------|-------------------------|
| 1 | Transient Peak Reverse Voltage | V_{RSM} | V | 90 | |
| 2 | Peak Reverse Voltage | V_{RM} | V | 90 | |
| 3 | Average Forward Current | $I_{F(AV)}$ | A | 2.0 | |
| 4 | Peak Surge Forward Current | I_{FSM} | A | 40 | Half sinewave, one shot |
| 5 | I^2t Limiting Value | I^2t | A^2s | 8.0 | $1msec < t < 10msec$ |
| 6 | Junction Temperature | T_j | $^{\circ}C$ | -40 to +150 | |
| 7 | Storage Temperature | T_{stg} | $^{\circ}C$ | -40 to +150 | |

* Electrical characteristics($T_a=25^{\circ}C$, unless otherwise specified)

| No. | Parameter | Symbol | Unit | Value | Conditions |
|-----|--|---------------|---------------|-----------|--------------------------------|
| 1 | Forward Voltage Drop | V_F | V | 0.85 max. | $I_F=2.0A$ |
| 2 | Reverse Leakage Current | I_R | μA | 200 max. | $V_R=V_{RM}$ |
| 3 | Reverse Leakage Current Under High Temperature | $H \cdot I_R$ | mA | 55 max. | $V_R=V_{RM}, T_j=150^{\circ}C$ |
| 4 | Thermal Resistance | $R_{th(j-l)}$ | $^{\circ}C/W$ | 20 max. | Between Junction and Lead |

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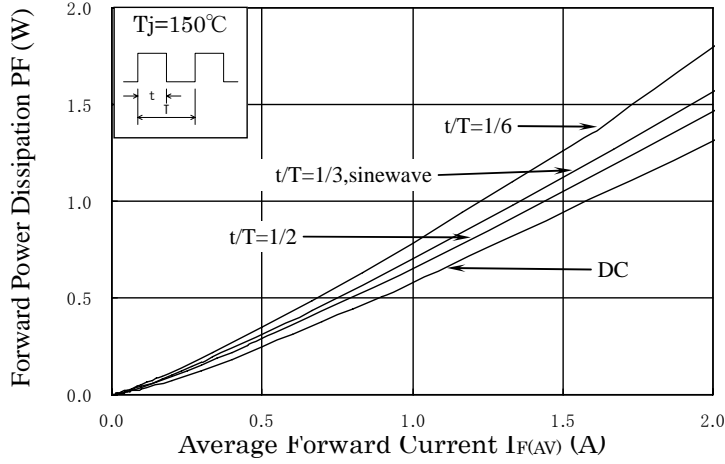
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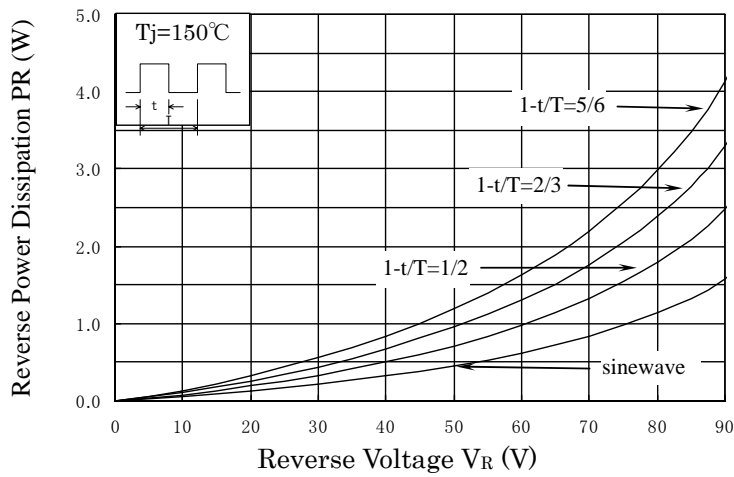
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★ Characteristics

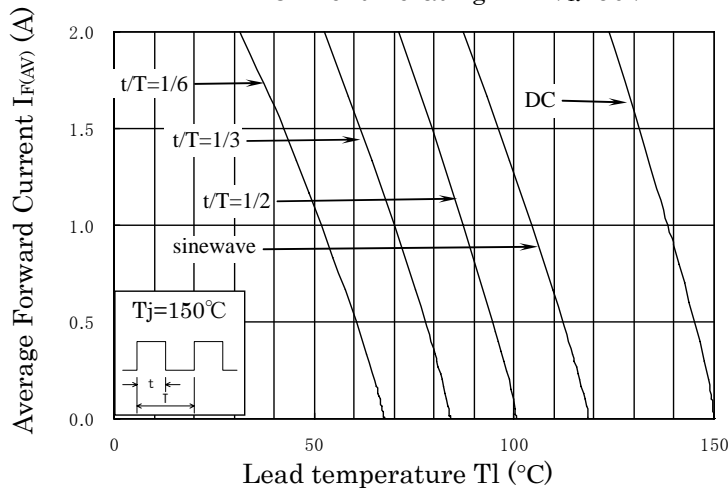
Forward Power Dissipation



Reverse Power Dissipation



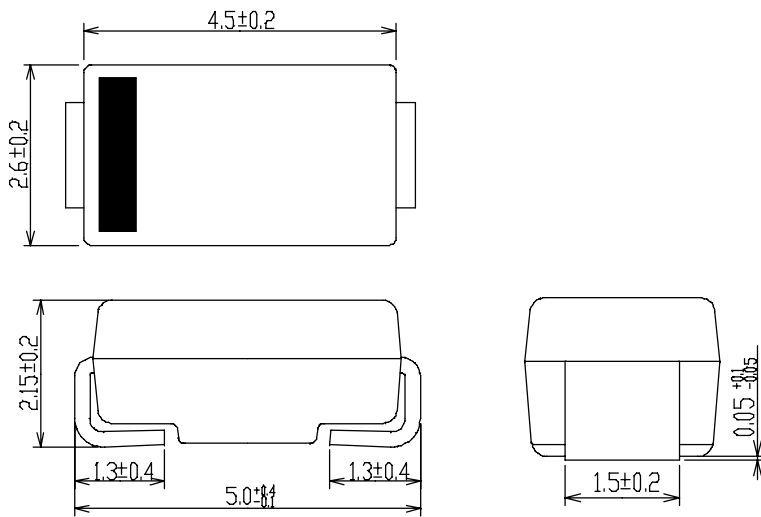
Current Derating $V_R=90\text{V}$



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★ Outline drawings, mm



★ Connection Diagram

